

## SPECIFICATION AMENDMENTS

Please amend the title of the application to read as follows:

### WAVELENGTH MULTIPLEXER/DEMULTIPLEXER

Please replace paragraph [0035] with the following:

[0035] As above, the thickness of the dielectric multilayer film 5 is 30 $\mu\text{m}$  and that of the substrate 51 is 5 $\mu\text{m}$ , so the dielectric multilayer film 5 and the substrate 51 are inserted into the groove 4. Therefore, the half of total thickness of 30 $\mu\text{m}$  + 5 $\mu\text{m}$  = 35 $\mu\text{m}$  (17.5 $\mu\text{m}$ ) is the distance from the multilayer surface 5s to the center of the dielectric multilayer filter including the substrate 51 [[groove 4]]. Also, since the distance X from the multilayer film surface 5s to the intersection point C1 of the optical waveguides is 6 $\mu\text{m}$ , the distance from the intersection point C1 of the optical waveguides to the center of the dielectric multilayer filter including the substrate 51 [[groove 4]] is 17.5 $\mu\text{m}$  - 6 $\mu\text{m}$  = 11.5 $\mu\text{m}$ .

Please replace paragraph [0036] with the following:

[0036] That is, the center of the dielectric multilayer filter including the substrate 51 [[groove 4]] is positioned at a distance of 11.5 $\mu\text{m}$  apart from the intersection point C1 of the optical waveguides, and the groove 4 is arranged to be perpendicular to the perpendicular bisector of the optical waveguides 2 and 3 and with a wider width than the total thickness of the dielectric multilayer film 5 by 2 $\mu\text{m}$  to 3 $\mu\text{m}$ .

Please replace paragraph [0053] with the following:

[0053] For the demultiplexing characteristic obtained by the reflection from the optical waveguide 2 to the optical waveguide 3, a flat and low-loss characteristic is obtained in the longer wavelength than 1550 nm [[ $\mu$ m]], shows as shown in FIG. 4, and the problem in the prior art, the increased loss in the long wavelength band is solved.

Please replace paragraph [0059] with the following:

[0059] In the experiment, the set position of the dielectric multilayer film 5 is changed from the position where the intersection point C1 is set at the multilayer film surface 5s (distance “X = 0” in FIG. 2A) to the position where the intersection point C1 is set at the boundary of the dielectric multilayer film 5 and the substrate 51 (distance “X = d” in FIG. 2C [[2B]]). The dielectric multilayer filter 5 is a short wavelength pass filter having an alternating multilayer of  $\text{SiO}_2$  and  $\text{Ta}_2\text{O}_5$  with a thickness of 30 $\mu\text{m}$  stacked on a polyimide thin-film substrate (substrate 51) with a thickness of 5 $\mu\text{m}$ , and its edge wavelength of the stop (reflection) band is set around 1530nm.